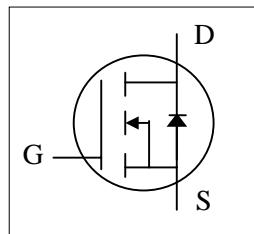
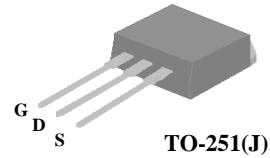
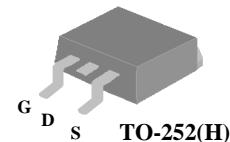




- ▼ Simple Drive Requirement
- ▼ Lower On-resistance
- ▼ Fast Switching Characteristic
- ▼ Halogen Free & RoHS Compliant



| | |
|--------------|------|
| BV_{DSS} | 60V |
| $R_{DS(ON)}$ | 36mΩ |
| I_D | 22A |



Description

AP9971A series are from Advanced Power innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance. The through-hole version (AP9971AGJ) are available for low-profile applications.

Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|---------------------------------|--------------------------------------|------------|-------|
| V_{DS} | Drain-Source Voltage | 60 | V |
| V_{GS} | Gate-Source Voltage | +20 | V |
| $I_D @ T_C = 25^\circ\text{C}$ | Drain Current, $V_{GS} @ 10\text{V}$ | 22 | A |
| $I_D @ T_C = 100^\circ\text{C}$ | Drain Current, $V_{GS} @ 10\text{V}$ | 14 | A |
| I_{DM} | Pulsed Drain Current ¹ | 80 | A |
| $P_D @ T_C = 25^\circ\text{C}$ | Total Power Dissipation | 34.7 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | °C |
| T_J | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Data

| Symbol | Parameter | Value | Units |
|-------------|-----------------------------------------------------------------------|-------|-------|
| R_{thj-c} | Maximum Thermal Resistance, Junction-case | 3.6 | °C/W |
| R_{thj-a} | Maximum Thermal Resistance, Junction-ambient (PCB mount) ³ | 62.5 | °C/W |
| R_{thj-a} | Maximum Thermal Resistance, Junction-ambient | 110 | °C/W |



AP9971AGH/J-HF

Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|----------------------------|------------------------------------------------|-------------------------------------------------------------|------|------|-----------|------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{\text{GS}}=0\text{V}, I_{\text{D}}=1\text{mA}$ | 60 | - | - | V |
| $R_{\text{DS}(\text{ON})}$ | Static Drain-Source On-Resistance ² | $V_{\text{GS}}=10\text{V}, I_{\text{D}}=15\text{A}$ | - | - | 36 | $\text{m}\Omega$ |
| | | $V_{\text{GS}}=6\text{V}, I_{\text{D}}=10\text{A}$ | - | - | 50 | $\text{m}\Omega$ |
| $V_{\text{GS}(\text{th})}$ | Gate Threshold Voltage | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\text{\mu A}$ | 1 | - | 3 | V |
| g_{fs} | Forward Transconductance | $V_{\text{DS}}=10\text{V}, I_{\text{D}}=15\text{A}$ | - | 12.4 | - | S |
| I_{DSS} | Drain-Source Leakage Current | $V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$ | - | - | 10 | \mu A |
| I_{GSS} | Gate-Source Leakage | $V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$ | - | - | ± 100 | nA |
| Q_g | Total Gate Charge | $I_{\text{D}}=15\text{A}$ | - | 17 | 27 | nC |
| Q_{gs} | Gate-Source Charge | $V_{\text{DS}}=48\text{V}$ | - | 2.5 | - | nC |
| Q_{gd} | Gate-Drain ("Miller") Charge | $V_{\text{GS}}=10\text{V}$ | - | 6.4 | - | nC |
| $t_{\text{d}(\text{on})}$ | Turn-on Delay Time | $V_{\text{DS}}=30\text{V}$ | - | 6.6 | - | ns |
| t_r | Rise Time | $I_{\text{D}}=15\text{A}$ | - | 22 | - | ns |
| $t_{\text{d}(\text{off})}$ | Turn-off Delay Time | $R_{\text{G}}=3.3\Omega$ | - | 17 | - | ns |
| t_f | Fall Time | $V_{\text{GS}}=10\text{V}$ | - | 4.3 | - | ns |
| C_{iss} | Input Capacitance | $V_{\text{GS}}=0\text{V}$ | - | 625 | 1000 | pF |
| C_{oss} | Output Capacitance | $V_{\text{DS}}=25\text{V}$ | - | 90 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | $f=1.0\text{MHz}$ | - | 65 | - | pF |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|---------------------------------|----------------------------------------------------|------|------|------|-------|
| V_{SD} | Forward On Voltage ² | $I_{\text{S}}=15\text{A}, V_{\text{GS}}=0\text{V}$ | - | - | 1.3 | V |
| t_{rr} | Reverse Recovery Time | $I_{\text{S}}=15\text{A}, V_{\text{GS}}=0\text{V}$ | - | 27 | - | ns |
| Q_{rr} | Reverse Recovery Charge | $dI/dt=100\text{A}/\mu\text{s}$ | - | 26 | - | nC |

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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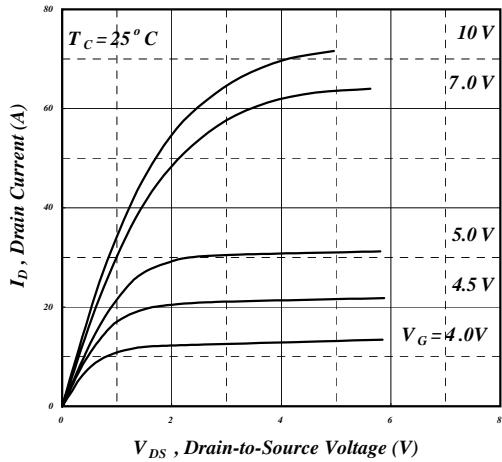


Fig 1. Typical Output Characteristics

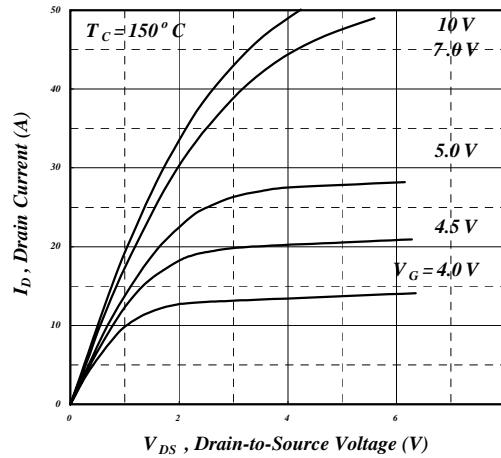


Fig 2. Typical Output Characteristics

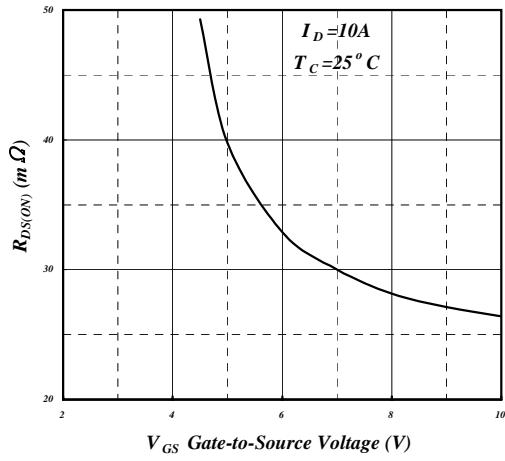


Fig 3. On-Resistance v.s. Gate Voltage

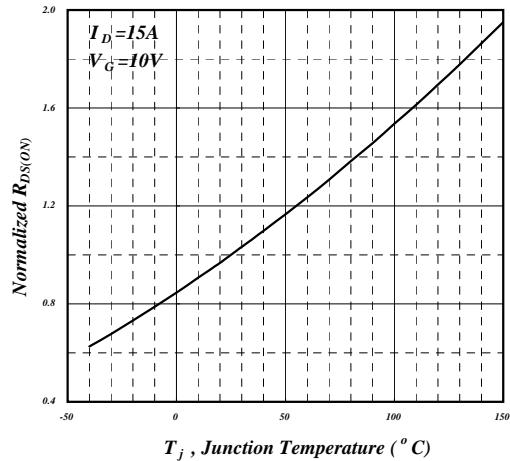


Fig 4. Normalized On-Resistance v.s. Junction Temperature

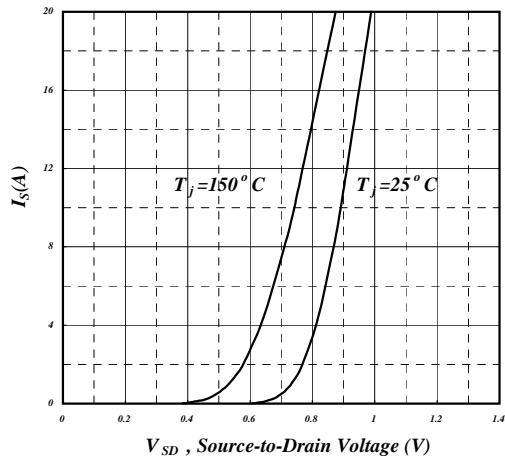


Fig 5. Forward Characteristic of Reverse Diode

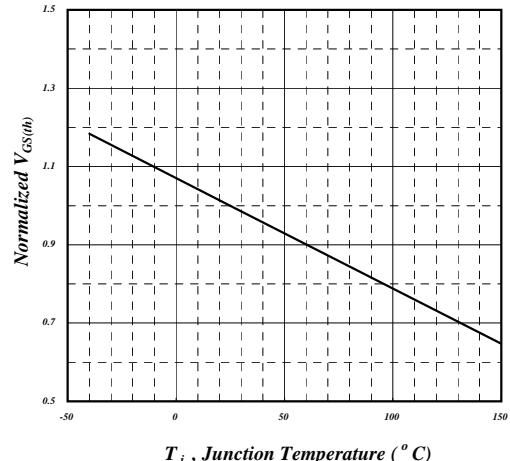
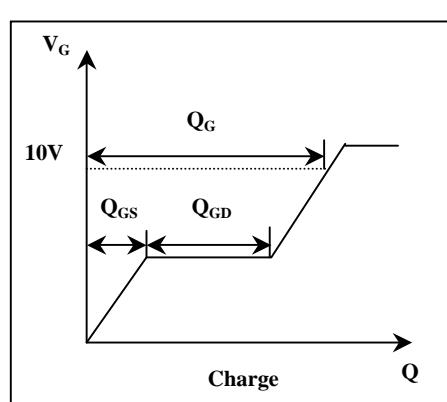
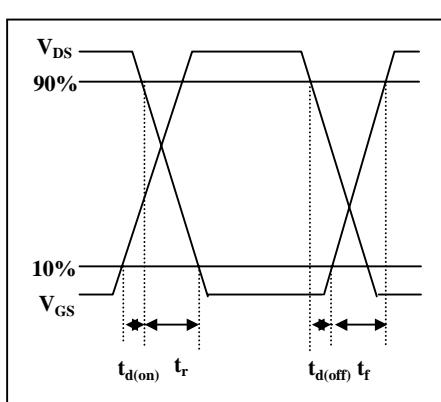
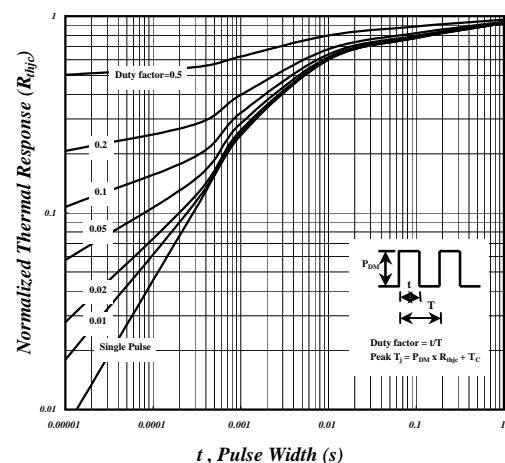
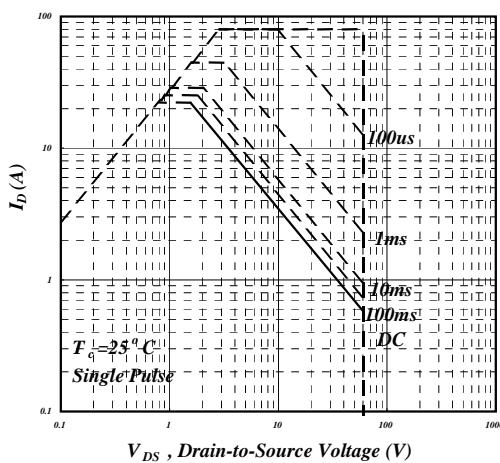
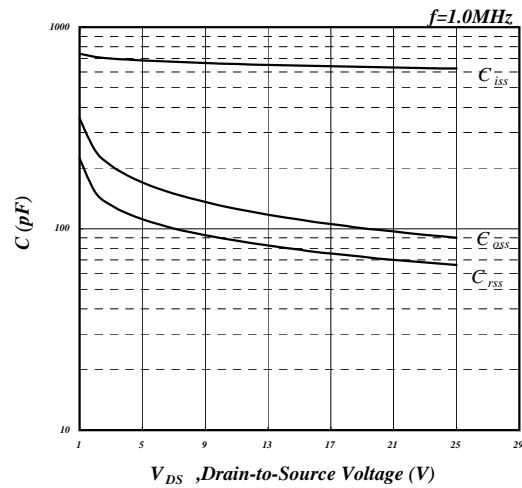
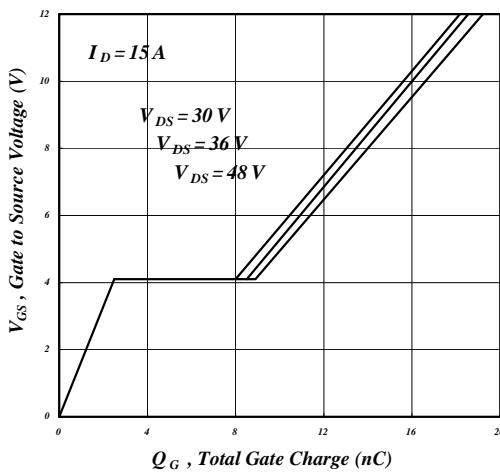


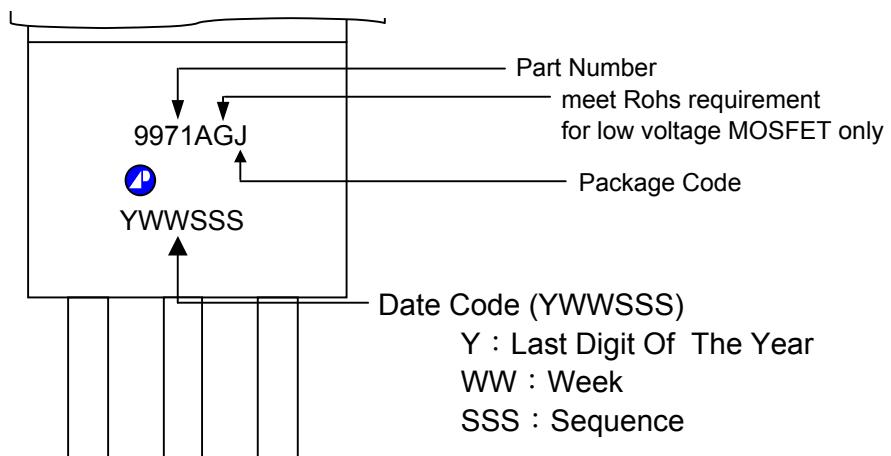
Fig 6. Gate Threshold Voltage v.s. Junction Temperature





MARKING INFORMATION

TO-251



TO-252

